

R2A20104/114 Series

Continuous Conduction Mode Interleaving PFC Control IC

R03DS0008EJ0301

Rev.3.01

Jan 08, 2016

Description

R2A20104/114 series is a boost converter control IC with PFC (Power Factor Correction). Employing continuous conduction mode interleaving PFC, it performs higher efficiency and lower switching noise even for high power use. The control of continuous conduction mode is carried out by detecting the current in power MOSFET. The R2A20114 series supports two types of current detection methods; current detection by current transformers (R2A20104SP/FP), and that by shunt resistors (R2A20114SP/FP). So that, it can be applicable for a variety of applications. Interleaving control of the boost converters, namely, producing 180 degrees phase shift between the output signals (GD1,2) driving the boost converters, enables the system to perform high conversion efficiency and low switching noises and, at the same time, to reduce ripple currents in input and output current and then this allows use of smaller components such as boost inductors, input filters and output capacitors. R2A20114 series integrates a various kinds of protection circuits, such as the detection circuit of breaking of wire in feedback loop, two modes of over voltage protection circuits, over current protection circuit and error output circuit (*1), which improve the reliability of the power supply system and reduce the number of component parts on the system.

Features

- Maximum Ratings
 - Supply voltage Vcc: 24 V
 - Junction temperature Tj: from -40 to +150 degrees centigrade
- Electrical characteristics
 - VFB feedback voltage VREF: 2.5 V ± 1.5%
 - UVLO (Undervoltage Lockout) operation start voltage VH: 10.4 V ± 0.7 V
 - UVLO operation shutdown voltage VL: 8.9 V ± 0.5 V
 - UVLO hysteresis voltage Hysvvl : 1.5 V ± 0.5 V
- Functions
 - Boost converter control with continuous conduction mode
 - Interleaving control
 - Frequency modulation (*2)
 - Brownout
 - Phase drop (*1)
 - External clock synchronization input
 - External clock synchronization output (*1)
 - Two modes of over voltage protections
 - Mode 1: Dynamic OVP preventing over voltage after sudden variation of load.
 - Mode 2: Static OVP preventing over voltage in the period of normal operation.
 - Feedback loop wire breaking/open detector
 - Dual over voltage protection circuits (*1): FB and OVP2 terminals
 - Current balance control
 - Phase 1 and Phase 2 independent over current protection
 - Package line-up
 - Pb-free LQFP-40 (R2A20104FP, R2A20114FP)
 - Pb-free SOP-20 (R2A20104SP, R2A20114SP)

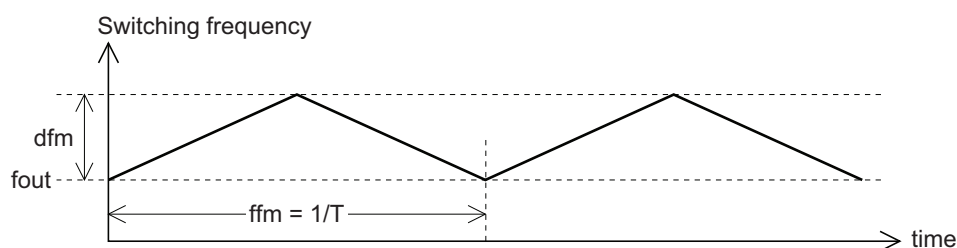
Notes: *1 Supported only by R2A20104FP and R2A20114FP

*2 Frequency modulation periods (dfm) of R2A20104SP and R2A20114SP are fixed.

The Function List of R2A20104/114 Series

Item		R2A20104SP	R2A20104FP	R2A20114SP	R2A20114FP
PFC control		Continuous conduction mode interleaving			
Current detection method		Current transformer		Shunt resistor	
Package		SOP-20	LQFP-40	SOP-20	LQFP-40
Protection circuits	Brownout detection	Supported	Supported	Supported	Supported
	2nd OVP	Not supported	Supported	Not supported	Supported
	Phase error	Not supported	Supported	Not supported	Supported
Noise reduction	Jitter generation (Frequency modulation)	Supported (But, frequency modulation period (dfm) ^(*1) is fixed)	Supported	Supported (But, frequency modulation period (dfm) ^(*1) is fixed)	Supported
Synchronization with external signal	Input	Supported	Supported	Supported	Supported
	Output	Not supported	Supported	Not supported	Supported
Efficiency improvement	Phase drop	Not supported	Supported	Not supported	Supported

Note: *1 Refer to the figure depicted below:

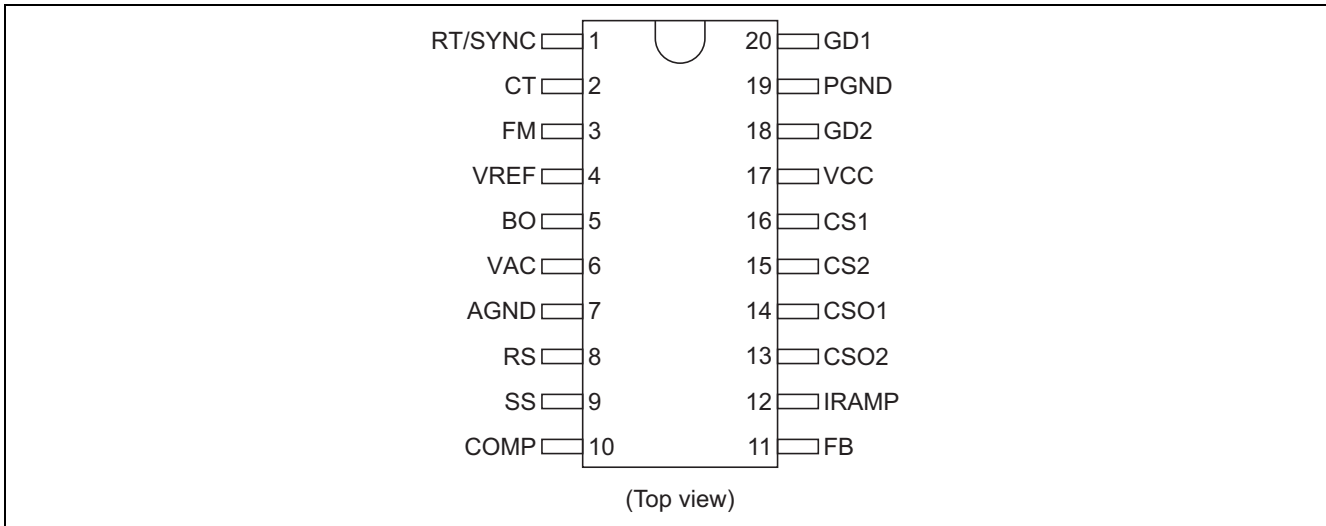


Ordering Information

Part No.	Package Name	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)	Remarks
R2A20104FPW0	FP-40EV	PLQP0040JB-C	FP	W (2000 pcs/reel)	non-HF
R2A20104FPW5					HF
R2A20114FPW0					non-HF
R2A20114FPW5					HF
R2A20104SPW0	FP-20DAV	PRSP0020DD-B	SP	W (2000 pcs/reel)	non-HF
R2A20104SPW5					HF
R2A20114SPW0					non-HF
R2A20114SPW5					HF

Note: HF: Halogen-Free

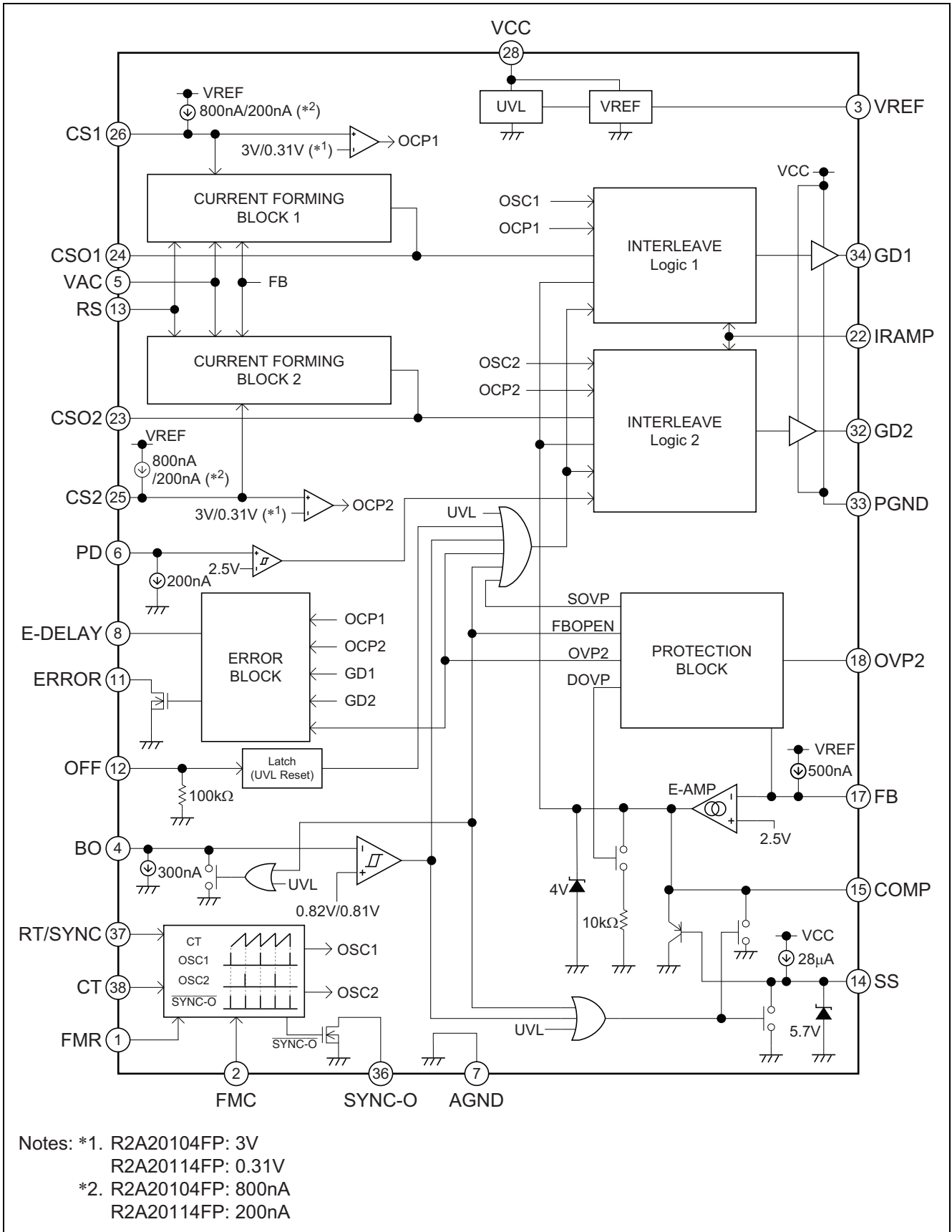
Pin Arrangement of R2A20104SP and R2A20114SP



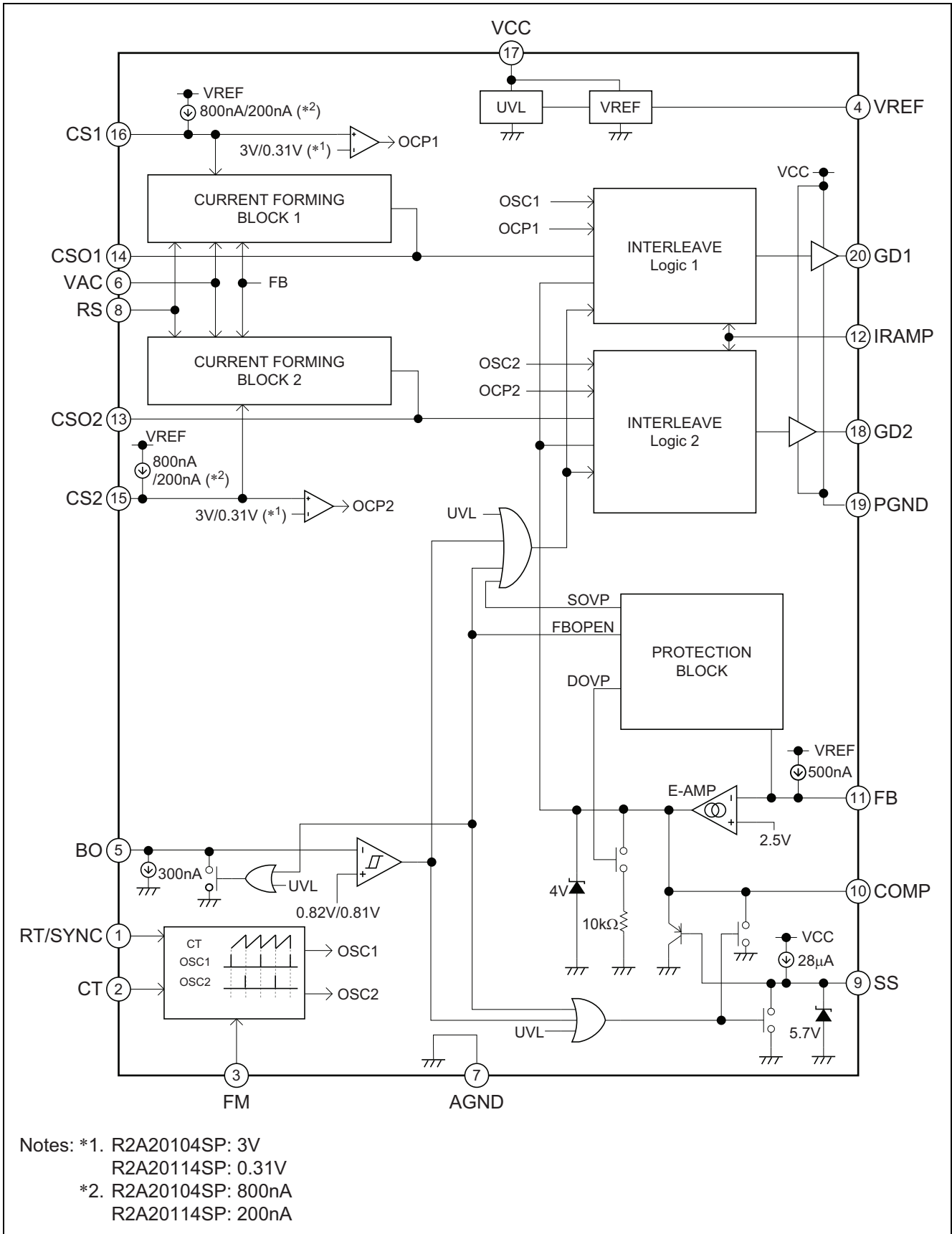
Pin Functions of R2A20104SP and R2A20114SP

Pin No.	Pin Name	Input/Output	Function
1	RT/SYNC	Input	Frequency setting timing resistor connecting terminal / Sync. signal input terminal
2	CT	Input	Frequency setting timing capacitor connecting terminal
3	FM	Input	Frequency modulation setting timing capacitor connecting terminal
4	VREF	Output	Reference voltage output terminal
5	BO	Input	Brownout input terminal
6	VAC	Input	AC voltage input terminal
7	AGND	—	Analog ground
8	RS	Input	Current correction setting resistor connecting terminal
9	SS	Input	Soft start setting capacitor connecting terminal
10	COMP	Output	Error amplifier output terminal (to be phase-compensated)
11	FB	Input	Error amplifier input terminal (feedback voltage input terminal)
12	IRAMP	Input	Ramp waveform setting resistor connecting terminal
13	CSO2	Output	Current sense amplifier 2 output terminal (to be phase-compensated)
14	CSO1	Output	Current sense amplifier Output 1 output terminal (to be phase-compensated)
15	CS2	Input	Current sense 2 input terminal
16	CS1	Input	Current sense 1 input terminal
17	VCC	Input	Supply voltage terminal
18	GD2	Output	Converter 2 Power MOSFET drive terminal
19	PGND	—	Power ground
20	GD1	Output	Converter 1 Power MOSFET drive terminal

Block Diagram of R2A20104FP and R2A20114FP



Block Diagram of R2A20104SP and R2A20114SP



Absolute Maximum Ratings

Item	Symbol	Value	Unit	Note	
Supply voltage	VCC	-0.3 to +24	V	3	
GD1 and 2	Peak current	l _{pk-gd1} , l _{pk-gd2}	±1	A	3, 4
	DC current	l _{dc-gd1} , l _{dc-gd2}	±0.1	A	3
Vref terminal current	I _{ref}	-5	mA	3	
Terminal current	I _{t-group}	±1	mA	3, 5	
RS terminal current	I _{rs}	-500	μA	3	
RT terminal current	I _{rt}	-200	μA	3	
RAMP terminal current	I _{ramp}	-200	μA	3	
BO clamp current	I _{bo}	300	μA	3	
Terminal voltage	V _{t-group}	-0.3 to V _{ref}	V	3, 6	
Vref terminal voltage	V _{t-ref}	-0.3 to V _{ref} +0.3	V	3	
SS terminal voltage	V _{t-ss}	-0.3 to V _{ref} +1	V	3	
Power dissipation	P _t	1	W	3, 7	
Operating ambient temperature	T _{a-opr}	-40 to +125	°C		
Junction temperature	T _j	-40 to +150	°C	8	
Storage temperature	T _{stg}	-55 to +150	°C		

- Notes:
- Rated voltages are with reference to the AGND and PGND terminal.
 - For the direction of Rated currents, (+) denotes the current flowing into the IC, and (-) denotes the current flowing out of the IC.
 - Ambience temperature, T_a is 25 degrees centigrade.
 - Transient current when driving a capacitive load.
 - Rated currents of the terminals listed below:
COMP, CSO1, CSO2
 - Rated voltages of the terminals listed below:
in the case of R2A20104FP/R2A20114FP: CS1, CS2, VAC, RS, FB, PD, BO, ERROR, E-DLAY, OFF, OVP2, FMC, FMR, RT/SYNC, IRAMP, SYNC-O, CT, COMP, CSO1, CSO2
in the case of R2A20104SP/R2A20114SP: CS1, CS2, VAC, RS, FB, BO, IRAMP, FM, RT/SYNC, CT, COMP, CSO1, CSO2
 - Thermal resistor
in the case of R2A20104FP/R2A20114FP: θ_{ja} = 85.3 degrees centigrade/W
in the case of R2A20104SP/R2A20114SP: θ_{ja} = 120 degrees centigrade/W
These values are obtained under the condition that the IC is mounted on the glass epoxy board, of which size is 50 × 50 × 1.6 [mm] and wiring density is 10%.
 - Stresses exceeding the absolute maximum ratings may damage the device.
These are stress ratings only. Functional operation above the recommended operating ambient temperature range is not implied.
Extended exposure to stresses above the absolute maximum ratings may affect device reliability.

Electrical Characteristics

($T_a = 25^\circ\text{C}$, $V_{CC} = 12\text{ V}$, $C_T = 1000\text{ pF}$, $R_T = 27\text{ k}\Omega$, $CS1, CS2 = \text{GND}$, $IRAMP = 10\text{ k}\Omega$, $BO = 1\text{ V}$, $V_{AC} = 0\text{ V}$, $RS = 220\text{ k}\Omega$, $FMC = \text{GND}$ (*¹), $FM = \text{GND}$ (*²), $FB = \text{COMP}$)

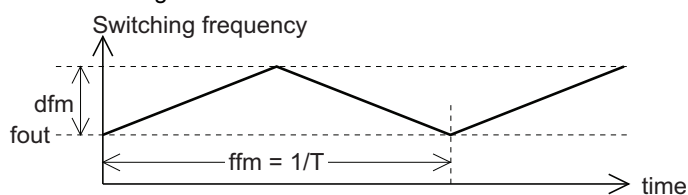
	Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Supply	UVLO turn-on threshold	Vuvlh	9.7	10.4	11.1	V	
	UVLO turn-off threshold	Vuvll	8.4	8.9	9.4	V	
	UVLO hysteresis	Hysuvt	1.0	1.5	2.0	V	
	Standby current	Istby	—	100	160	μA	$V_{CC} = 8.9\text{ V}$
	Operating current	Icc	—	5	7.5	mA	
VREF	Output voltage	Vref	4.85	5.00	5.15	V	Isource = -1 mA
	Line regulation	Vref-line	—	5	20	mV	Isource = -1 mA, $V_{CC} = 10\text{ V to }24\text{ V}$
	Load regulation	Vref-load	—	5	20	mV	Isource = -1 mA to -5 mA
	Temperature stability	dVref	—	± 80	—	$\text{ppm}/^\circ\text{C}$	$T_a = -40\text{ to }125^\circ\text{C}$ (* ³)
Error amplifier	Feedback voltage	Vfb	2.462	2.500	2.538	V	FB-COMP Short
	Input bias current	Ifb	-0.8	-0.5	-0.2	μA	Measured pin: FB
	Open loop gain	Av	—	40	—	dB	(* ³)
	Upper clamp voltage	Vclamp-comp	3.8	4.0	4.3	V	FB = 2.0 V, COMP: Open
	Low voltage	Vl-comp	0.0	0.1	0.3	V	FB = 3.0 V, COMP: Open
	Source current	Isrc-comp	-190	-135	-80	μA	FB = 1.5 V, COMP = 2.5 V
	Sink current 1	I _{snk-comp1}	—	120	—	μA	(* ³)
	Sink current 2	I _{snk-comp2}	220	320	420	μA	FB = 3.5 V, COMP = 2.5 V
Brownout	Transconductance	gm	120	200	290	μs	FB = 2.45 V \leftrightarrow 2.55 V, COMP = 2.5 V
	PFC enable voltage	Von-pfc	0.74	0.82	0.9	V	Input pin: BO
	PFC disable voltage	Voff-pfc	0.73	0.81	0.89	V	Input pin: BO
Oscillator	Initial accuracy	fout	70	78	86	kHz	Measured pin: OUT, FMC = 0 V
	fout temperature stability	dfout/dTa	—	± 0.1	—	$\%/^\circ\text{C}$	$T_a = -40\text{ to }125^\circ\text{C}$ (* ³)
	fout voltage stability	fout-line	-1.5	0.5	1.5	%	$V_{CC} = 12\text{ V to }18\text{ V}$
	CT top voltage	Vct-H	—	3.6	4.0	V	(* ³)
	RT voltage	Vrt	1.15	1.25	1.35	V	
	FMC sink current (* ¹)/ FM sink current (* ²)	I _{snk-fmc} (* ¹)/ I _{snk-fm} (* ²)	6	11	16	μA	FMC = 1 V (* ¹)/ FM = 1 V (* ²)
	FMC source current (* ¹)/ FM source current (* ²)	I _{src-fmc} (* ¹)/ I _{src-fm} (* ²)	-16.5	-11.5	-6.5	μA	FMC = 1 V (* ¹)/ FM = 1 V (* ²)
	FM magnitude change	dfm	19	24	29	kHz	FMC = 5 V (* ¹)/FM = 5 V (* ²) (* ³ , * ⁴)
	FM frequency 1 (* ¹)	ffm1	0.25	0.38	0.5	kHz	FMC = 6.8 nF, FMR = 4 V (* ⁴)
	FM frequency 2 (* ¹)	ffm2	14	25	35	kHz	FM = 220 pF, FMR = 1.2 V (* ⁴)
	FM frequency (* ²)	ffm	6	10	14	kHz	FMC = 220 pF (* ⁴)

Notes: *1 Applied to R2A20104FP, R2A20114FP

*2 Applied to R2A20104SP, R2A20114SP

*3 Design Specification (Reference data)

*4 Refer to the figure shown below:



Electrical Characteristics (cont.)

(Ta = 25°C, VCC = 12 V, CT = 1000 pF, RT = 27 kΩ, CS1, CS2 = GND, IRAMP = 10 kΩ, BO = 1 V, VAC = 0 V, RS = 220 kΩ, FMC = GND (*1), FM = GND (*2), FB = COMP)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	
Synchroni- zation	SYNC threshold voltage (rising)	Vsync	2.0	2.5	3.0	V	
	SYNC Min. pulse	Psync	2	—	—	μs	
	SYNC-OUT shunt current (*1)	Isync-s	5.0	—	—	mA	
	SYNC-OUT leakage current (*1)	Isync-l	—	—	1.0	μA	
Current slope	RS output voltage 1	Vrs1	0.56	0.65	0.74	V	VAC = 0 V, VFB = 2.5 V
	RS output voltage 2	Vrs2	0.04	0.14	0.26	V	VAC = 2.5 V, VFB = 0 V
	VAC bias current	Ivac	-0.4	-0.2	-0.05	μA	Measured pin: VAC
Soft start	Source current	Iss	-40	-28	-16	μA	SS = 2 V
Phase drop	Phase drop threshold voltage (*1)	Vpd	2.4	2.5	2.6	V	
	Phase drop hysteresis (*1)	Hya-pd	150	200	250	mV	
	PD bias current (*1)	Ipd	0.05	0.2	0.5	μA	Measured pin: PD
AMP1, 2	CSO offset voltage1 (*5)	Voffset	0.68	0.88	1.0	V	Vcs = 0 V
	CSO offset voltage1 (*6)	Voffset	0.54	0.74	0.86	V	Vcs = 0 V
	CSO offset voltage2	Vcaoh	2.83	3	3.17	V	Vcs = 0.24 V (*5), Vcs = 2.3 V (*6)
	CS Bias current (*5)	Ics-r	-0.4	-0.2	-0.05	μA	Measured pin: CS1, 2
	CS Bias current (*6)	Ics-ct	-1.1	-0.8	-0.5	μA	Measured pin: CS1, 2
Gate drive 1, 2	Gate drive rise time	tr-gd	—	30	100	ns	CL = 500 pF
	Gate drive fall time	tf-gd	—	30	100	ns	CL = 500 pF
	Gate drive low voltage	Vol1-gd	—	0.05	0.2	V	Isink = 10 mA
		Vol2-gd	—	1	1.25	V	Isink = 0.25 mA, VCC = 5 V
	Gate drive high voltage	Voh-gd	11.5	11.9	—	V	Isource = -10 mA
	Minimum duty cycle	Dmin-out	—	—	0	%	
Maximum duty cycle	Dmax-out	90	95	98	%		
Over voltage protection	Dynamic OVP Threshold voltage	Vdovp	VFB× 1.025	VFB× 1.040	VFB× 1.055	V	
	Static OVP Threshold voltage	Vsovp	VFB× 1.065	VFB× 1.080	VFB× 1.095	V	COMP = OPEN
	Static OVP Hysteresis	Hys-sovp	30	80	130	mV	COMP = OPEN
	OVP2 Threshold voltage (*1)	Vovp2	VFB× 1.065	VFB× 1.080	VFB× 1.095	μA	
	OVP2 Hysteresis (*1)	Hys-ovp2	30	80	130	mV	COMP = OPEN
	OVP2 Bias current (*1)	Iovp2	-0.5	-0.3	-0.05	μA	Measured pin: OVP2
	FB Open Detect Threshold voltage	Vfbopen	0.45	0.5	0.55	V	
	FB Open Detect hysteresis	Vfbopen	0.16	0.2	0.24	V	
Over current protection	OCP Threshold voltage (*5)	VCL	0.28	0.31	0.34	V	
	OCP Threshold voltage (*6)	VCL	2.9	3	3.1	V	
	Delay to output	td-CL	—	100	250	ns	

Notes: *1 Applied to R2A20104FP, R2A20114FP

*2 Applied to R2A20104SP, R2A20114SP

*5 Applied to R2A20114FP, R2A20114SP

*6 Applied to R2A20104FP, R2A20104SP

Electrical Characteristics (cont.)

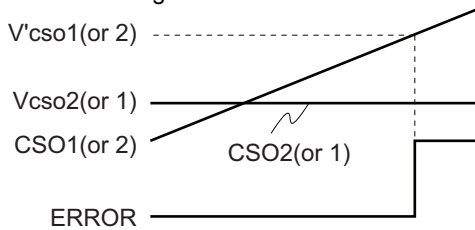
(Ta = 25°C, VCC = 12 V, CT = 1000 pF, RT = 27 kΩ, CS1, CS2 = GND, IRAMP = 10 kΩ, BO = 1 V, VAC = 0 V, RS = 220 kΩ, FMC = GND (*1), FM = GND (*2), FB = COMP)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	
Error signal	ERROR shunt current (*1)	lerror-s	5.0	—	—	mA	
	ERROR leakage current (*1)	lerror-l	—	—	1.0	μA	
	Phase error detect point	Perror	1.1	1.35	1.6	—	Vcso1 or 2 = 2.5 V, Vcso2 or 1: sweep (*7)
	OFF threshold voltage (*1)	Voff	3.3	4.0	4.7	V	
	E-DELAY charge current (*1)	led-c	-55	-36	-20	μA	
	E-DELAY discharge current (*1)	led-d	20	36	55	μA	
	E-DELAY threshold voltage (*1)	Vdelay	2.35	2.45	2.55	V	

Notes: *1 Applied to R2A20104FP, R2A20114FP

*2 Applied to R2A20104SP, R2A20114SP

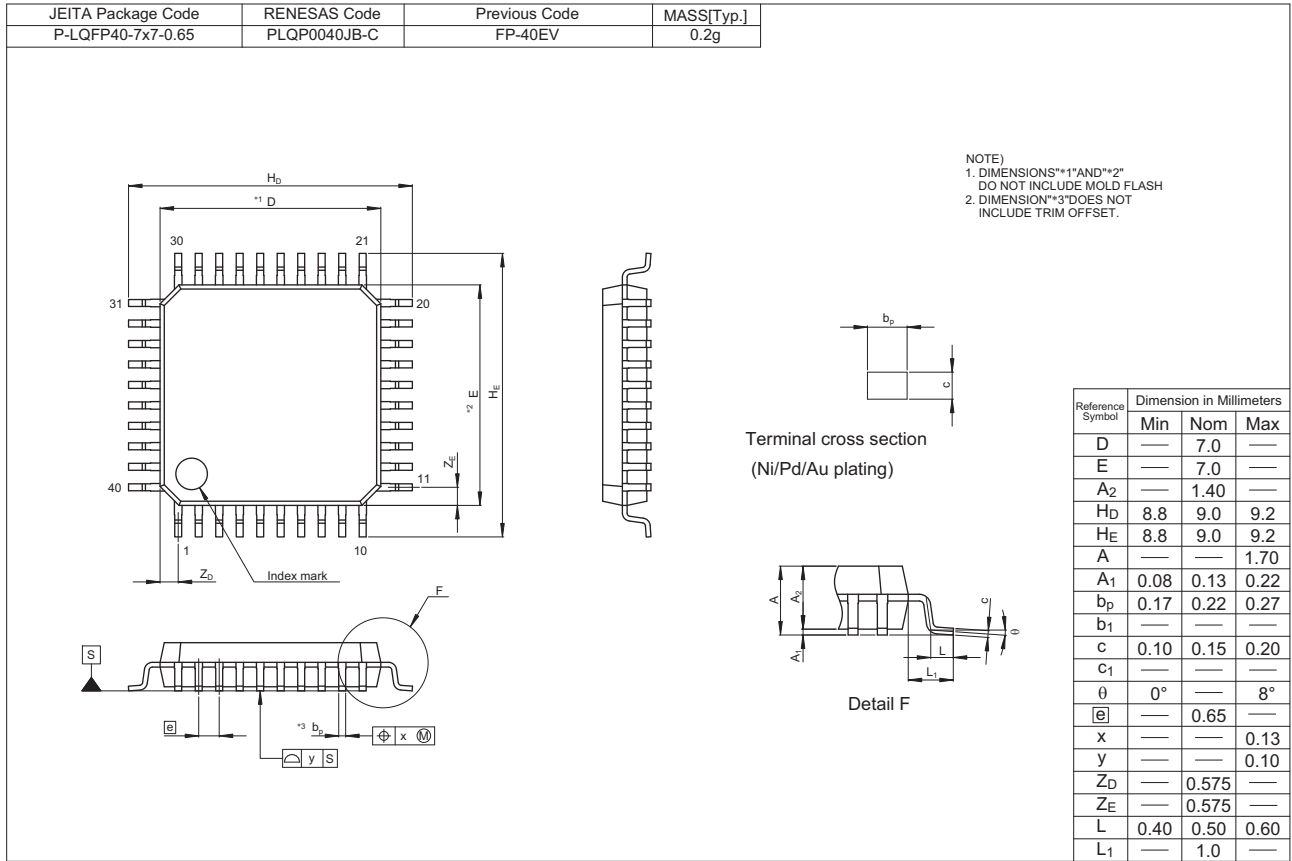
*7 Refer to the figure shown below:



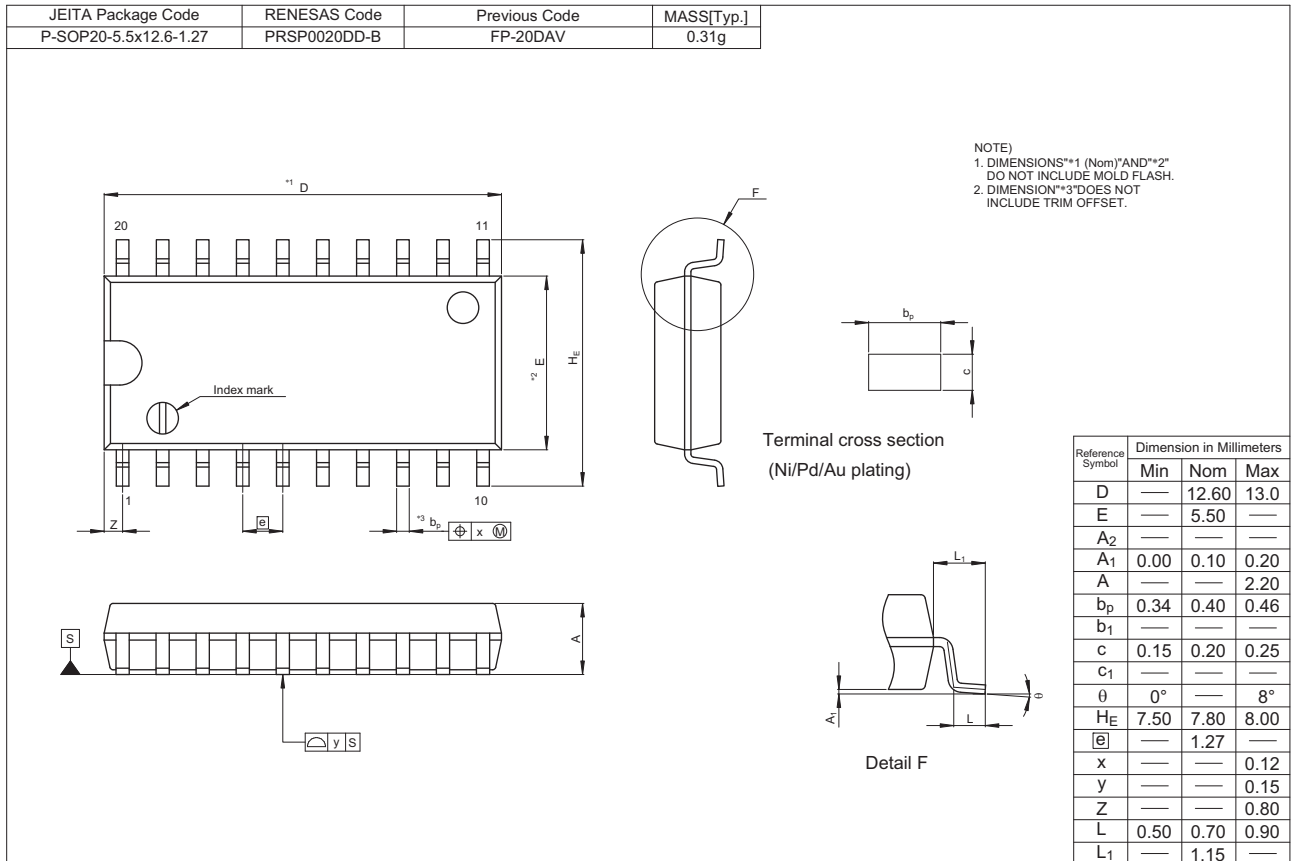
$$P_{\text{error}} = \frac{V'_{\text{cso1(or 2)}}[\text{V}] - 0.55[\text{V}]}{V_{\text{cso2(or 1)}}[\text{V}] - 0.55[\text{V}]}$$

Package Dimensions

• R2A20104FP and R2A20114FP



• R2A20104SP and R2A20114SP



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Renesas Electronics America Inc.

2801 Scott Boulevard Santa Clara, CA 95050-2549, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited

9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3
Tel: +1-905-237-2004

Renesas Electronics Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.

Room 1709, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100191, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.

Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited

Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852 2886-9022

Renesas Electronics Taiwan Co., Ltd.

13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

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80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.

Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.

No.77C, 100 Feet Road, HAL II Stage, Indiranagar, Bangalore, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.

12F., 234 Teheran-ro, Gangnam-Gu, Seoul, 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141